



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H1015

AUDIO FREQUENCY AMPLIFIER

HIGH FREQUENCY OSC

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

T_{stg} —Storage Temperature..... $-55\sim 150^{\circ}\text{C}$

T_j —Junction Temperature..... 150°C

P_C —Collector Dissipation..... 400mW

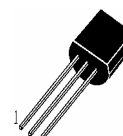
V_{CBO} —Collector-Base Voltage..... -50V

V_{CEO} —Collector-Emitter Voltage..... -50V

V_{EBO} —Emitter-Base Voltage..... -5V

I_C —Collector Current..... -150mA

TO-92



1—Emitter, E

2—Collector, C

3—Base, B

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

| Symbol | Characteristics | Min | Typ | Max | Unit | Test Conditions |
|-----------------------------|---------------------------------------|-----|-----|------|------|--|
| I_{CBO} | Collector Cut-off Current | | | -100 | nA | $V_{\text{CB}}=-50\text{V}$, $I_{\text{E}}=0$ |
| I_{EBO} | Emitter Cut-off Current | | | -100 | nA | $V_{\text{EB}}=-5\text{V}$, $I_{\text{C}}=0$ |
| $H_{\text{FE}}(1)$ | DC Current Gain | 70 | | 700 | | $V_{\text{CE}}=-6\text{V}$, $I_{\text{C}}=-2\text{mA}$ |
| $H_{\text{FE}}(2)$ | | 25 | | | | $V_{\text{CE}}=-6\text{V}$, $I_{\text{C}}=-150\text{mA}$ |
| $V_{\text{CE}}(\text{sat})$ | Collector- Emitter Saturation Voltage | | | -0.3 | V | $I_{\text{C}}=-100\text{mA}$, $I_{\text{B}}=-10\text{mA}$ |
| $V_{\text{BE}}(\text{sat})$ | Base-Emitter Saturation Voltage | | | -1.1 | V | $I_{\text{C}}=-100\text{mA}$, $I_{\text{B}}=-10\text{mA}$ |
| BV_{CBO} | Collector-Base Breakdown Voltage | -50 | | | V | $I_{\text{C}}=-100\mu\text{A}$, $I_{\text{E}}=0$ |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | -50 | | | V | $I_{\text{C}}=-1\text{mA}$, $I_{\text{B}}=0$ |
| BV_{EBO} | Emitter-Base Breakdown Voltage | -5 | | | V | $I_{\text{E}}=-10\mu\text{A}$, $I_{\text{C}}=0$ |
| f_{T} | Current Gain-Bandwidth Product | 80 | | | MHz | $V_{\text{CE}}=-10\text{V}$, $I_{\text{C}}=-1\text{mA}$ |

h_{FE} Classification

O

Y

GR

BL1

BL2

70—140

120—240

200—400

350—510

480—700